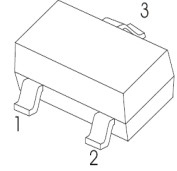




SOT-23 Plastic-Encapsulate Transistors

KTC3265 TRANSISTOR (NPN)

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

FEATURES

- High DC current gain
- Complementary to KTA1298

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	800	mA
P _C	Collector Power Dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30 V, I _E =0			0.1	μA
Collector cut-off current	I _{EBO}	V _{EB} =5 V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =1V, I _C = 100mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =20mA			0.5	V
base-emitter voltage	V _{BE}	V _{CE} =1V, I _C =10mA	0.5		0.8	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA f=100MHz		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	EO	EY

Typical Characteristics

KTC3265

